

Magnetocrystalline anisotropy and antiferromagnetic phase transition in PrRh_2Si_2

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Abstract

We present magnetic and transport properties of PrRh_2Si_2 single crystals which exhibit antiferromagnetic order below $T_N = 68$ K. Well defined anomalies due to magnetic phase transition are observed in magnetic susceptibility, resistivity, and specific heat data. The T_N of 68 K for PrRh_2Si_2 is much higher than 5.4 K expected on the basis of de-Gennes scaling. The magnetic susceptibility data reveal strong uniaxial anisotropy in this compound similar to that of PrCo_2Si_2 . With increasing pressure T_N increases monotonically up to $T_N = 71.5$ K at 22.5 kbar.

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Introduction

YbRh_2Si_2 has been widely investigated due to its proximity to a quantum phase transition [1, 2, 3, 4]. We show in this paper that its Pr-homolog PrRh_2Si_2 also presents unique magnetic properties. All the investigated RRh_2Si_2 (R = rare earth) compounds have been found to order antiferromagnetically [1, 5, 6, 7, 8, 9, 10, 11, 12]. Among them GdRh_2Si_2 has the highest ordering temperature, $T_N \sim 106$ K [6]. EuRh_2Si_2 exhibits complex magnetic order with an antiferromagnetic ordering below 25 K [11]. CeRh_2Si_2 and YbRh_2Si_2 have unusual and interesting magnetic properties which are discussed below.

The antiferromagnetic ordering temperature $T_N \sim 36$ K in CeRh_2Si_2 is very high compared to the de-Gennes expected ordering temperature of 1.2 K [12, 13]. One more transition is observed at 24 K. The exact nature (localized versus itinerant) of the magnetism of CeRh_2Si_2 is not yet settled. The pressure dependence of T_N and of the magnetic moment indicates an itinerant nature of the magnetism [13]. The itinerant character of magnetism in CeRh_2Si_2 has also been suggested from a systematic study of doping at Rh sites in $\text{Ce}(\text{Rh}_{1-x}\text{Pd}_x)_2\text{Si}_2$ [14]. However, the dHvA study suggests local moment magnetism in CeRh_2Si_2 at ambient pressure. Under the application of pressure the Fermi surface topology changes discontinuously leading to an itinerant moment magnetism above the critical pressure of around 1 GPa [15]. Pressure induced superconductivity has been observed around 1 GPa below 0.5 K [16, 17].

Heavy-fermion YbRh_2Si_2 has an antiferromagnetic ordering temperature T_N of ~ 70 mK [1]. The antiferromagnetic order can be suppressed very easily by application of magnetic field or by substitution of Si by Ge, leading to a quantum critical point [2, 3, 4]. Electrical transport, thermodynamic and thermal expansion data reveal that quantum critical point in YbRh_2Si_2 is of local nature in contrast to the spin density wave type quantum critical point in CeCu_2Si_2 [18, 19].

Crystal field effects can have strong influence on the properties of Pr-compounds. For example, the low lying crystal field excitations are responsible for the heavy fermion behavior in unconventional superconductor $\text{PrOs}_4\text{Sb}_{12}$ [20, 21, 22]. Despite numerous investigations on RRh_2Si_2 , we did not find any discussion in literature on the properties of PrRh_2Si_2 . In this paper we report magnetization, specific heat, electrical resistivity and magnetoresistance of PrRh_2Si_2 single crystals. In addition, we also carried out pressure dependent electrical

resistivity measurements.

Sample preparation and measurements

Single crystals of PrRh_2Si_2 were grown from indium flux as well as using floating zone method in a mirror furnace (CSI Japan). Appropriate amounts of high purity elements (Pr: 99.99%, La: 99.9%, Rh: 99.999% and Si: 99.9999%) were arc melted several times on a water cooled copper hearth under argon atmosphere. The arc melted polycrystalline PrRh_2Si_2 and indium were taken in a molar ratio of 1:20 in an alumina crucible, which was then sealed inside a tantalum crucible with a partial pressure of argon gas. The sealed tantalum crucible was heated to 1450 °C under argon atmosphere for two hours and then cooled down to 900 °C at a rate of 5 °C/hour. Below 900°C rate of cooling was increased to 300 °C/hour. Indium flux was removed by etching with dilute hydrochloric acid. We obtained single crystals of about 2.5 mm x 1.5 mm x 0.4 mm by this method. We also succeeded in growing PrRh_2Si_2 single crystal using float zone mirror furnace using 10 mm/h growth rate and counter-rotation of seed and feed rods. The diameter of the float zone grown crystal was about 6 mm.

Samples were characterized by copper K_α X-ray diffraction and scanning electron microscope (SEM) equipped with energy dispersive X-ray analysis (EDAX). Laue method was used to orient the single crystals. A commercial SQUID magnetometer was used to measure magnetization. Specific heat was measured using relaxation method in a physical property measurement system (PPMS–Quantum design). Electrical resistivity was measured by standard ac four probe technique using AC-transport option of PPMS. Pressure studies of the electrical resistivity up to 2.3 GPa and in the temperature range $3\text{ K} < T < 300\text{ K}$ were carried out utilizing a clamp-type double layer pressure cell consisting of an inner cylinder made of NiCrAl and an outer body of Cu:Be. Silicone oil served as pressure transmitting medium. The pressure inside the cell was determined at low temperature by the inductively measured shift of the superconducting transition temperature of lead.

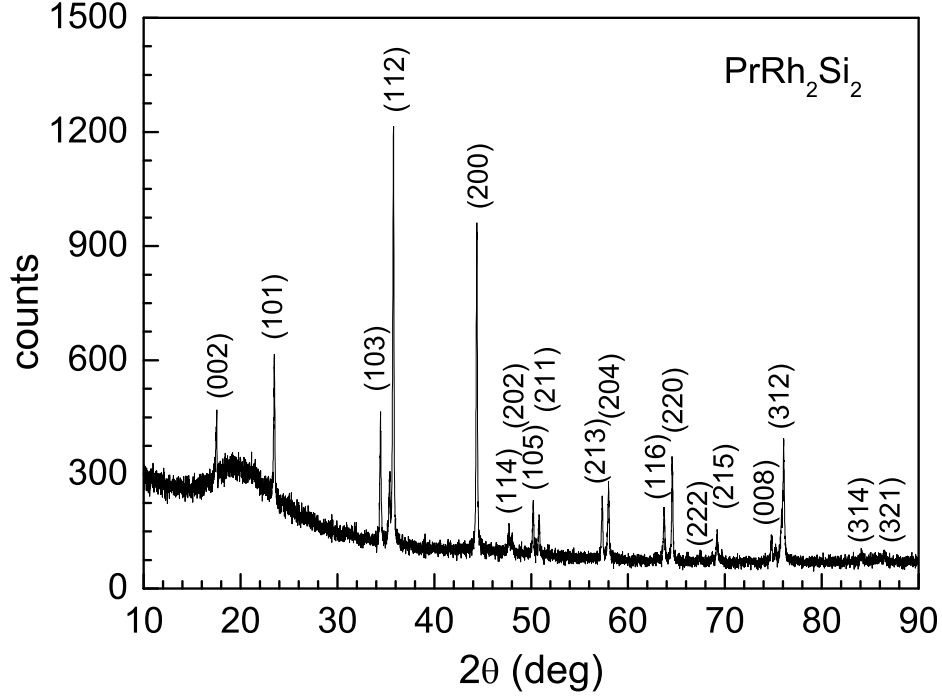


FIG. 1: Indexed powder x-ray diffraction pattern of ThCr_2Si_2 -type body-centered-tetragonal pulverized PrRh_2Si_2 single crystal (flux grown).

Results and Discussion

From the analysis of powder X-ray diffraction data of the crushed single crystals (figure 1), we find that PrRh_2Si_2 crystallizes in ThCr_2Si_2 -type tetragonal structure (space group $I4/mmm$) with the lattice parameters $a = 0.4079$ nm, $c = 1.0138$ nm, and the unit cell volume = 0.16876 nm³ for the flux grown sample, and $a = 0.4078$ nm, $c = 1.0138$ nm, and the unit cell volume = 0.16858 nm³ for the float zone grown sample. The X-ray diffraction and SEM image confirmed the samples to be single phase. The EDAX composition analysis confirmed the desired stoichiometric composition of 1:2:2.

The temperature dependence of the magnetic susceptibility of PrRh_2Si_2 single crystal is shown in figure 2 for magnetic field applied along the a - b plane and the c -axis. A large anisotropy in the magnetic susceptibility $\chi(T)$ is observed. The susceptibility data have much larger values for $B//c$ compared to that for $B//a$ - b implying the easy axis to be the c -axis. This anisotropic behavior is similar to the strong uniaxial anisotropy along c -

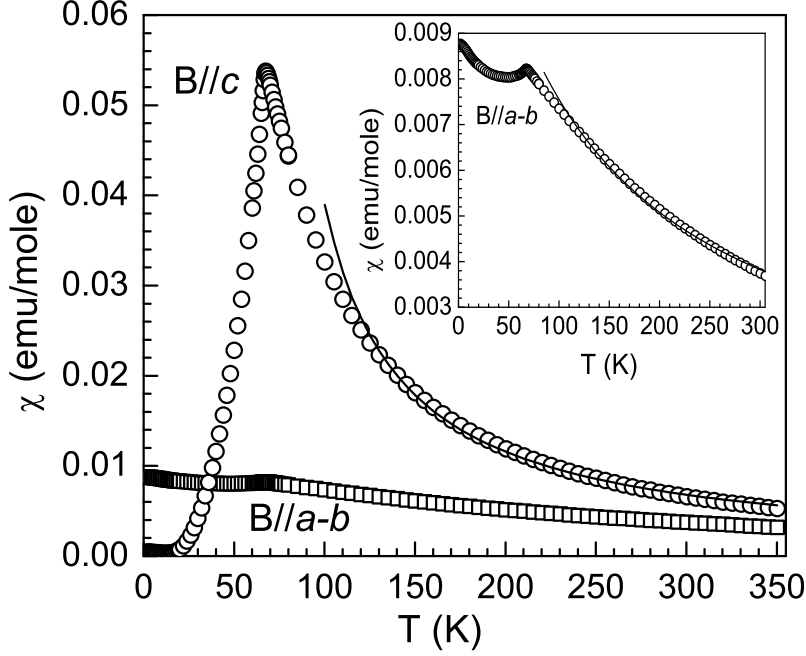


FIG. 2: Temperature dependence of magnetic susceptibility of PrRh_2Si_2 single crystal (flux grown) measured in a field of 3.0 T. Inset shows the enlarged view of $B//a-b$ data. The solid lines represent fit to Curie-Weiss behaviour.

axis in CeRh_2Si_2 [10] but different from the easy plane behavior observed in YbRh_2Si_2 [1]. Within a series of $R\text{-T-X}$ compound, the change of the magnetic anisotropy with changing the R -element is governed by the change in α_J second order Stevens factor within the CEF Hamiltonian [23]. A change from a uniaxial behavior in CeRh_2Si_2 and PrRh_2Si_2 to an easy plane behavior in YbRh_2Si_2 is in full accordance with $\alpha_J < 0$ for Ce- and Pr- while $\alpha_J > 0$ for Yb-compound. Since in all three cases the anisotropy is very pronounced, it indicates a very large and positive A_2^0 CEF-parameter in the whole RRh_2Si_2 series. An antiferromagnetic transition is observed in the susceptibility data at 68 K for both $B//a-b$ and $B//c$. As expected for an antiferromagnet T_N decreases with increasing magnetic field ($T_N = 66.5$ K at $B = 5$ T). The susceptibility data exhibit slight deviation from the Curie-Weiss behaviour $\chi(T) = C/(T-\theta_p)$ for both $B//a-b$ and $B//c$ due to the effect of crystal fields. From the linear fit of inverse susceptibility data (100 K – 300 K) at 3 T we obtain the effective magnetic moment $\mu_{eff} = 3.48 \mu_B$ (very close to the theoretical value of $3.58 \mu_B$ for Pr^{3+} ions) and

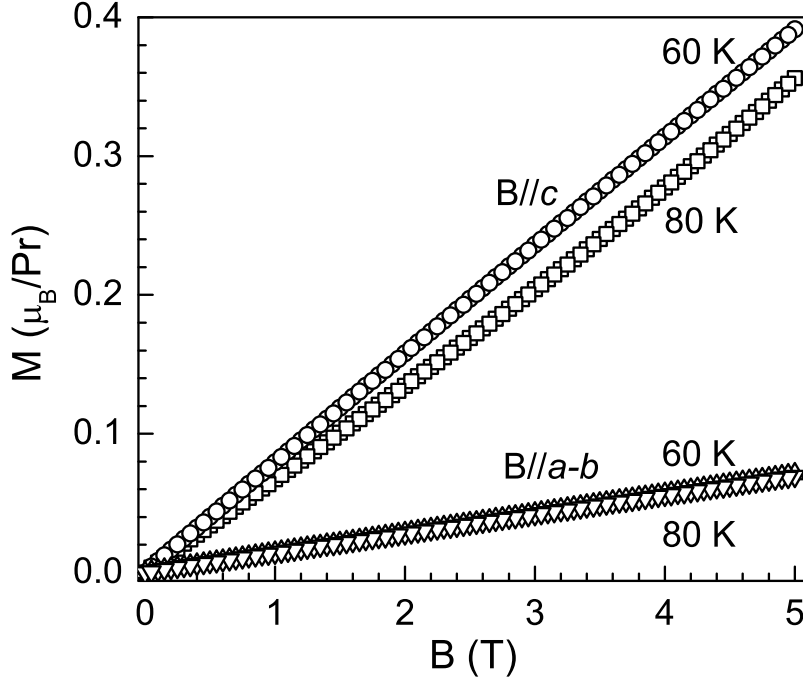


FIG. 3: Field dependence of isothermal magnetization of PrRh_2Si_2 single crystal (flux grown) at 60 and 80 K along $B//c$ and $B//a-b$.

the Curie-Weiss temperature $\theta_p^a = -103.2$ K for $B//a-b$, and $\mu_{eff} = 3.63 \mu_B$ and $\theta_p^c = +57.9$ K for $B//c$. Further, we note a very pronounced peak and a rapid decrease of magnetic susceptibility to essentially zero value below 20 K for $B//c$ and a much weaker temperature dependence for $B//a-b$, which suggests strongly anisotropic Ising-type antiferromagnetism in PrRh_2Si_2 similar to that of PrCo_2Si_2 [24].

The isothermal magnetization data exhibit a linear dependence on field at 60 K (magnetically ordered state) and 80 K (paramagnetic state) for both $B//a-b$ and $B//c$ (figure 3). The magnetic moments at 5 T are very small in both the directions ($0.07 \mu_B/\text{Pr}$ for $B//a-b$ and $0.39 \mu_B/\text{Pr}$ for $B//c$) and the maximum value attained is only 12% of the saturation magnetization for Pr^{3+} ion ($3.2 \mu_B/\text{Pr}$). Measurements at higher fields are required to observe the metamagnetic transitions which are expected in antiferromagnets with strong magneto-crystalline anisotropy.

The specific heat data of single crystal PrRh_2Si_2 (indium flux grown) together with that of the nonmagnetic reference compound LaRh_2Si_2 are shown in figure 4. The specific heat

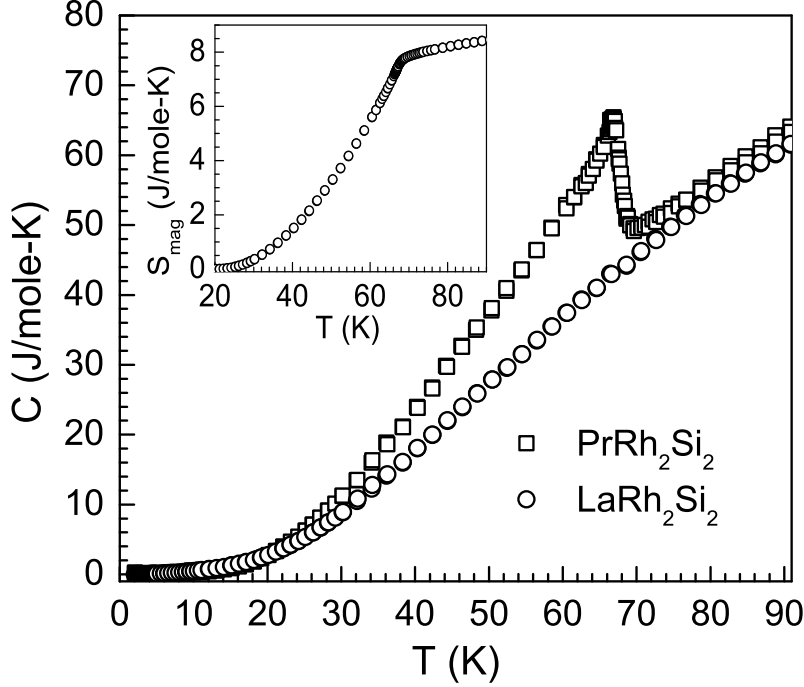


FIG. 4: Temperature dependence of the specific heat of single crystal PrRh_2Si_2 (flux grown) and polycrystalline LaRh_2Si_2 in the temperature range 2 to 90 K. The inset shows the magnetic contribution to the entropy of PrRh_2Si_2 .

of PrRh_2Si_2 exhibits a pronounced λ -type anomaly at 68 K, which confirms the intrinsic nature of antiferromagnetic ordering in this compound. The float zone grown single crystal of PrRh_2Si_2 also exhibits a similar well defined anomaly at 68 K due to antiferromagnetic order. The specific heat data of PrRh_2Si_2 and LaRh_2Si_2 hardly differ from each other below 20 K showing that the magnetic excitations have vanished exponentially below 20 K. This indicates a large gap in the magnetic excitation spectra in the ordered state, which can obviously be attributed to the strong Ising-type anisotropy observed in the magnetic susceptibility data. The linear coefficient to the specific heat is $\gamma \sim 18$ mJ/mole-K². The temperature dependence of the magnetic entropy is shown as inset in figure 4. At 70 K the magnetic entropy attains a value of 7.85 J/mole-K, which is 36% more than $R\ln 2$ and 14 % lower than $R\ln 3$. Thus, either three singlets or one singlet and one doublet CEF levels are in the energy-range below 80 K and involved in the magnetic ordering. Because of the huge uniaxial anisotropy and the general trend of the CEF parameters within the RRh_2Si_2

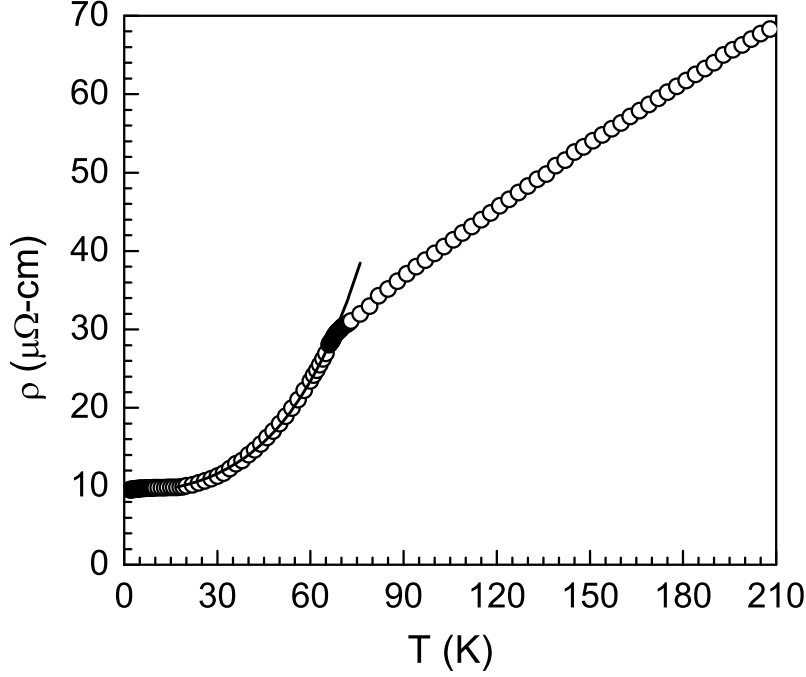


FIG. 5: Temperature dependence of electrical resistivity ($I//a-b$) of flux grown PrRh_2Si_2 single crystal in the temperature range 1.8 – 210 K. Solid line shows the fit to gapped magnon characteristics in the ordered state, i.e. $\rho(T) = \rho_0 + AT^2 + C \left\{ \frac{1}{5}T^5 + \Delta T^4 + \frac{5}{3}\Delta^2 T^3 \right\} \exp(-\Delta/T)$.

series, one can suspect that these lowest CEF levels are the two Γ_1 singlets and either the Γ_2 singlet or the Γ_5 doublet [25].

The electrical resistivity measured with ac current flowing in the $a-b$ plane is shown in figure 5. The resistivity shows typical metallic behavior with room temperature resistivity ρ_{300K} of $85 \mu\Omega\text{-cm}$, residual resistivity $\rho_0 \sim 9.6 \mu\Omega\text{-cm}$ and residual resistivity ratio (RRR) ~ 9 . A linear decrease of resistivity is observed with decreasing temperature until it meets the antiferromagnetic transition at 68 K, below which the resistivity shows a large decrease. In the ordered state the resistivity data present gapped magnon characteristics and fit well to the relation [26]

$$\rho(T) = \rho_0 + AT^2 + C \left\{ \frac{1}{5}T^5 + \Delta T^4 + \frac{5}{3}\Delta^2 T^3 \right\} \exp(-\Delta/T)$$

below 65 K (inset of figure 5) where $\rho_0 = 9.8 \mu\Omega\text{-cm}$ is the residual resistivity, $A =$

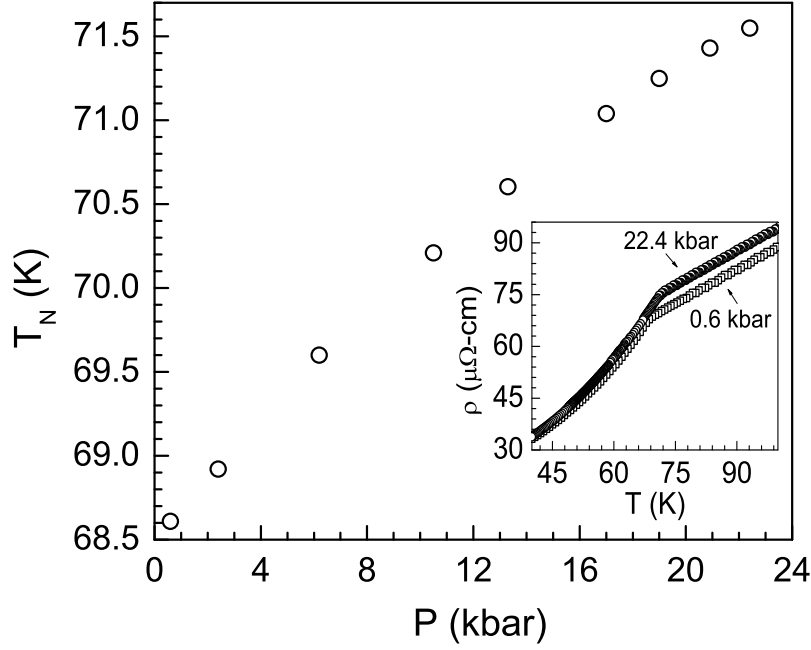


FIG. 6: T_N of PrRh_2Si_2 as a function of externally applied pressure. The inset shows temperature dependence of resistivity under pressure.

$0.00241 \mu\Omega\text{-cm}/\text{K}^2$ is the coefficient to the Fermi liquid term, $C = 8.96 \times 10^{-9} \mu\Omega\text{-cm}/\text{K}^5$ is the prefactor to the magnon contribution, and $\Delta = 37.8 \text{ K}$ is the magnon energy gap.

As both CeRh_2Si_2 and YbRh_2Si_2 exhibit strong pressure dependence in the electrical resistivity we have performed resistivity measurement on PrRh_2Si_2 under externally applied pressure. Up to 22.5 kbar there is no pronounced effect of externally applied pressure on the resistivity except an increase of T_N from 68.5 K at $p = 0$ to 71.5 K at $p = 22.5$ kbar (figure 6). Similar weak effect of pressure on the magnetically ordered state was also found in PrCo_2Si_2 [27].

From the de-Gennes scaling in the family of RRh_2Si_2 ($R = \text{rare earths}$) one would expect an ordering temperature of 5.4 K in PrRh_2Si_2 . While in CeRh_2Si_2 the anomalously high T_N might be a result of the mixture of localized and itinerant character of the magnetic order we can not offer any clear reason for the high T_N of PrRh_2Si_2 . Enhanced density of states as in the case of GdRh_2Si_2 and large value of exchange constant (as evidenced by large θ_p) definitely contribute to higher value of T_N . It is also found that RRh_2Si_2 compounds which have higher values of T_N than expected on the basis of de-Gennes scaling have their

moments aligned along c -axis below T_N . PrRh_2Si_2 also has higher T_N than expected and the magnetic susceptibility data suggest that Pr moments lie along c -axis in this case also. We suspect the uniaxial anisotropy which forces the moment to lie along the c -axis is also responsible for the high T_N in PrRh_2Si_2 . System with uniaxial anisotropy has much larger value of magnetic susceptibility for $B//(\text{easy-axis})$ which helps in the process of magnetic ordering. Thus T_N for a system with uniaxial anisotropy will be higher than that of an isotropic system or a weakly anisotropic system.

Conclusion

We succeeded in growing single crystals of PrRh_2Si_2 which forms in ThCr_2Si_2 -type body-centered tetragonal structure. Temperature dependent magnetic susceptibility, electrical resistivity, specific heat data reveal strongly anisotropic Ising type antiferromagnetic order below 68 K in this compound. Application of pressure up to 22.5 kbar does not stabilize any new ordered phase but T_N increases from 68 K to 71.5 K.

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